

MOSFETs Silicon N-channel MOS (U-MOSIX-H)

# TPN2R805PL

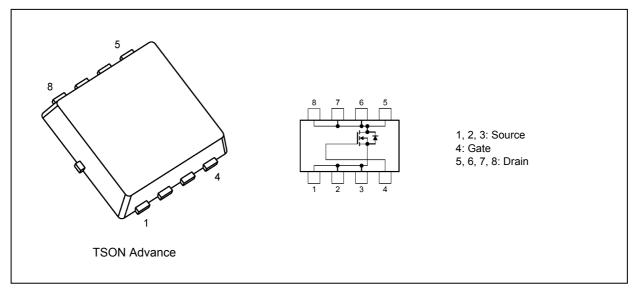
## 1. Applications

- · High-Efficiency DC-DC Converters
- Switching Voltage Regulators
- · Motor Drivers

#### 2. Features

- (1) High-speed switching
- (2) Small gate charge:  $Q_{SW} = 12 \text{ nC (typ.)}$
- (3) Small output charge:  $Q_{oss} = 32 \text{ nC (typ.)}$
- (4) Low drain-source on-resistance:  $R_{DS(ON)} = 2.2 \text{ m}\Omega$  (typ.) ( $V_{GS} = 10 \text{ V}$ )
- (5) Low leakage current:  $I_{DSS}$  = 10  $\mu A$  (max) ( $V_{DS}$  = 45 V)
- (6) Enhancement mode:  $V_{th} = 1.4 \text{ to } 2.4 \text{ V (V}_{DS} = 10 \text{ V}, I_D = 0.3 \text{ mA)}$

## 3. Packaging and Internal Circuit



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## 4. Absolute Maximum Ratings (Note) (Ta = 25 °C unless otherwise specified)

| Characteristics                |                          |                    | Symbol           | Rating     | Unit |
|--------------------------------|--------------------------|--------------------|------------------|------------|------|
| Drain-source voltage           |                          |                    | $V_{DSS}$        | 45         | V    |
| Gate-source voltage            |                          |                    | $V_{GSS}$        | ±20        |      |
| Drain current (DC)             | (T <sub>c</sub> = 25 °C) | (Note 1)           | I <sub>D</sub>   | 80         | Α    |
| Drain current (DC)             | (Silicon limit)          | (Note 1), (Note 2) |                  | 139        |      |
| Drain current (pulsed)         | (t = 100 μs)             | (Note 1)           | I <sub>DP</sub>  | 200        |      |
| Power dissipation              | (T <sub>c</sub> = 25 °C) |                    | $P_{D}$          | 104        | W    |
| Power dissipation              |                          | (Note 3)           |                  | 2.67       |      |
| Power dissipation              |                          | (Note 4)           |                  | 0.63       |      |
| Single-pulse avalanche energy  |                          | (Note 5)           | E <sub>AS</sub>  | 34         | mJ   |
| Single-pulse avalanche current |                          | (Note 5)           | I <sub>AS</sub>  | 80         | Α    |
| Channel temperature            |                          |                    | T <sub>ch</sub>  | 175        | °C   |
| Storage temperature            |                          |                    | T <sub>stg</sub> | -55 to 175 |      |

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

#### 5. Thermal Characteristics

| Characteristics                       | Symbol                   | Max      | Unit                  |      |      |
|---------------------------------------|--------------------------|----------|-----------------------|------|------|
| Channel-to-case thermal resistance    | (T <sub>c</sub> = 25 °C) |          | R <sub>th(ch-c)</sub> | 1.43 | °C/W |
| Channel-to-ambient thermal resistance | (T <sub>a</sub> = 25 °C) | (Note 3) | R <sub>th(ch-a)</sub> | 56   |      |
| Channel-to-ambient thermal resistance | (T <sub>a</sub> = 25 °C) | (Note 4) | R <sub>th(ch-a)</sub> | 235  |      |

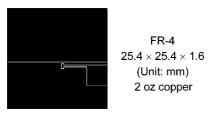
Note 1: Ensure that the channel temperature does not exceed 175 °C.

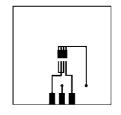
Note 2: Limited 80 A by package capability.

Note 3: Device mounted on a glass-epoxy board (a), Figure 5.1

Note 4: Device mounted on a glass-epoxy board (b), Figure 5.2

Note 5:  $V_{DD}$  = 36 V,  $T_{ch}$  = 25 °C (initial), L = 4.2  $\mu$ H,  $I_{AS}$  = 80 A





FR-4 25.4 × 25.4 × 1.6 (Unit: mm) 2 oz copper

Fig. 5.1 Device Mounted on a Glass-Epoxy Board (a)

Fig. 5.2 Device Mounted on a Glass-Epoxy Board (b)

Note: This transistor is sensitive to electrostatic discharge and should be handled with care.



#### 6. Electrical Characteristics

# 6.1. Static Characteristics (T<sub>a</sub> = 25 °C unless otherwise specified)

| Characteristics                         | Symbol               | Test Condition                                    | Min | Тур. | Max  | Unit |
|---|----------------------|---|-----|------|------|------|
| Gate leakage current                    | I <sub>GSS</sub>     | $V_{GS} = \pm 20 \text{ V}, V_{DS} = 0 \text{ V}$ | _   | _    | ±0.1 | μА   |
| Drain cut-off current                   | I <sub>DSS</sub>     | V <sub>DS</sub> = 45 V, V <sub>GS</sub> = 0 V     | _   | _    | 10   |      |
| Drain-source breakdown voltage          | V <sub>(BR)DSS</sub> | I <sub>D</sub> = 10 mA, V <sub>GS</sub> = 0 V     | 45  | _    | _    | ٧    |
| Drain-source breakdown voltage (Note 6) | V <sub>(BR)DSX</sub> | I <sub>D</sub> = 10 mA, V <sub>GS</sub> = -20 V   | 30  | _    | _    |      |
| Gate threshold voltage                  | $V_{th}$             | V <sub>DS</sub> = 10 V, I <sub>D</sub> = 0.3 mA   | 1.4 | _    | 2.4  |      |
| Drain-source on-resistance              | R <sub>DS(ON)</sub>  | V <sub>GS</sub> = 4.5 V, I <sub>D</sub> = 15 A    | _   | 3.2  | 5.0  | mΩ   |
|   |                      | V <sub>GS</sub> = 10 V, I <sub>D</sub> = 40 A     | _   | 2.2  | 2.8  |      |

Note 6: If a reverse bias is applied between gate and source, this device enters  $V_{(BR)DSX}$  mode. Note that the drain-source breakdown voltage is lowered in this mode.

# 6.2. Dynamic Characteristics (T<sub>a</sub> = 25 °C unless otherwise specified)

| Characteristics                | Symbol           | Test Condition   | Min | Тур. | Max  | Unit |
|--------------------------------|------------------|--|-----|------|------|------|
| Input capacitance              | C <sub>iss</sub> | V <sub>DS</sub> = 22.5 V, V <sub>GS</sub> = 0 V, f = 1 MHz | _   | 2450 | 3200 | pF   |
| Reverse transfer capacitance   | C <sub>rss</sub> |  | _   | 56   | 105  |      |
| Output capacitance             | C <sub>oss</sub> |  | _   | 610  | _    |      |
| Gate resistance                | r <sub>g</sub>   | _  | _   | 0.5  | 1.0  | Ω    |
| Switching time (rise time)     | t <sub>r</sub>   | See Fig. 6.2.1   | _   | 7.4  | _    | ns   |
| Switching time (turn-on time)  | t <sub>on</sub>  |  | _   | 17   | _    |      |
| Switching time (fall time)     | t <sub>f</sub>   |  | _   | 12   | _    |      |
| Switching time (turn-off time) | t <sub>off</sub> |  | _   | 34   | _    |      |

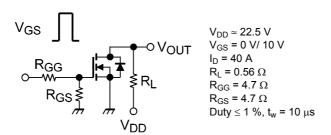


Fig. 6.2.1 Switching Time Test Circuit

# 6.3. Gate Charge Characteristics (T<sub>a</sub> = 25 °C unless otherwise specified)

| Characteristics                     | Symbol           | Test Condition  | Min | Тур. | Max | Unit |
|-------------------------------------|------------------|---|-----|------|-----|------|
| Total gate charge (gate-source plus | $Q_g$            | $V_{DD} \approx 22.5 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 40 \text{ A}$    | -   | 39   | 1   | nC   |
| gate-drain)                         |                  | $V_{DD} \approx 22.5 \text{ V}, V_{GS} = 4.5 \text{ V}, I_{D} = 15 \text{ A}$ |     | 19   |     |      |
| Gate-source charge 1                | Q <sub>gs1</sub> | $V_{DD} \approx 22.5 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 40 \text{ A}$    |     | 9.5  |     |      |
| Gate-drain charge                   | $Q_{gd}$         |   | _   | 7.1  |     |      |
| Gate switch charge                  | $Q_{SW}$         |   | _   | 12   | _   |      |
| Output charge                       | $Q_{oss}$        | V <sub>DS</sub> = 22.5 V, V <sub>GS</sub> = 0 V, f = 1 MHz                    | _   | 32   |     |      |



# 6.4. Source-Drain Characteristics (T<sub>a</sub> = 25 °C unless otherwise specified)

| Characteristics                         | Symbol                           | Test Condition  | Min | Тур. | Max  | Unit |
|---|----------------------------------|---|-----|------|------|------|
| Reverse drain current (pulsed) (Note 7) | I <sub>DRP</sub><br>(t = 100 μs) | _   | 1   | ı    | 200  | Α    |
| Diode forward voltage                   | $V_{DSF}$                        | I <sub>DR</sub> = 80 A, V <sub>GS</sub> = 0 V                   | 1   |      | -1.2 | V    |
| Reverse recovery time                   | t <sub>rr</sub>                  | V <sub>R</sub> = 22.5 V, I <sub>DR</sub> = 20 A,                | _   | 34   | _    | ns   |
| Reverse recovery charge                 | Q <sub>rr</sub>                  | $V_{GS} = 0 \text{ V}, -dI_{DR}/dt = 100 \text{ A/}\mu\text{s}$ | 1   | 27   | _    | nC   |

Note 7: Ensure that the channel temperature does not exceed 175 °C.

# 7. Marking

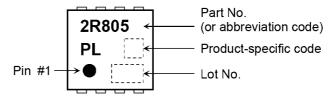


Fig. 7.1 Marking



## 8. Characteristics Curves (Note)

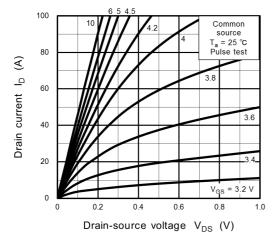


Fig. 8.1 I<sub>D</sub> - V<sub>DS</sub>

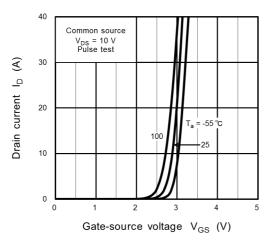


Fig. 8.3  $I_D - V_{GS}$ 

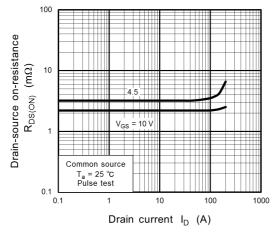


Fig. 8.5 R<sub>DS(ON)</sub> - I<sub>D</sub>

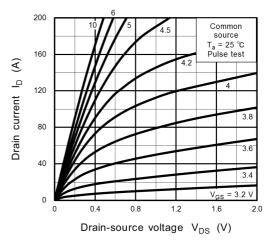


Fig. 8.2 I<sub>D</sub> - V<sub>DS</sub>

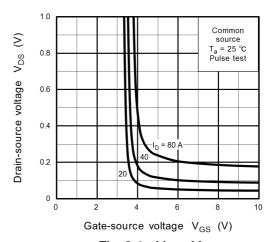


Fig. 8.4 V<sub>DS</sub> - V<sub>GS</sub>

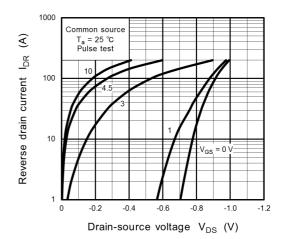


Fig. 8.6 IDR - VDS

Rev.2.0



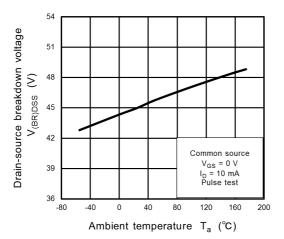


Fig. 8.7 V<sub>(BR)DSS</sub> - T<sub>a</sub>

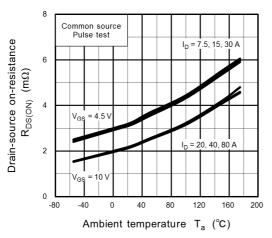


Fig. 8.9 R<sub>DS(ON)</sub> - T<sub>a</sub>

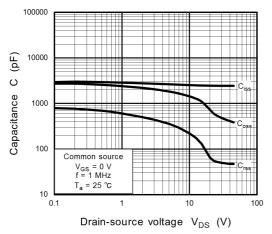


Fig. 8.11 Capacitance - V<sub>DS</sub>

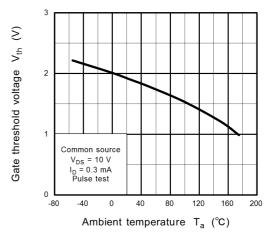


Fig. 8.8 V<sub>th</sub> - T<sub>a</sub>

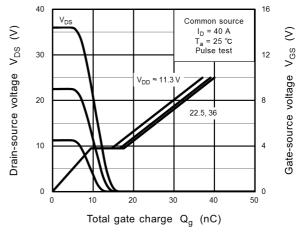


Fig. 8.10 Dynamic Input/Output Characteristics

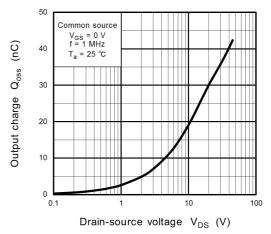


Fig. 8.12 Qoss - VDS



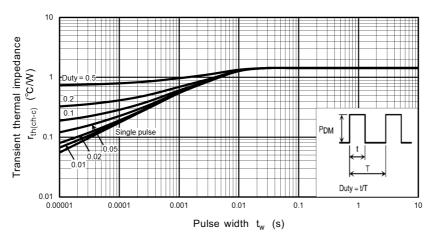


Fig. 8.13 r<sub>th</sub> - t<sub>w</sub> (Guaranteed Maximum)

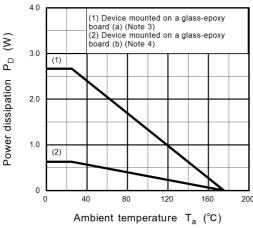


Fig. 8.14 P<sub>D</sub> - T<sub>a</sub> (Guaranteed Maximum)

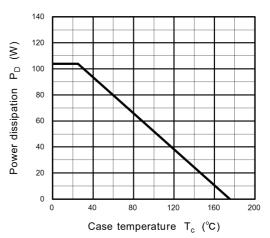


Fig. 8.15 P<sub>D</sub> - T<sub>c</sub> (Guaranteed Maximum)

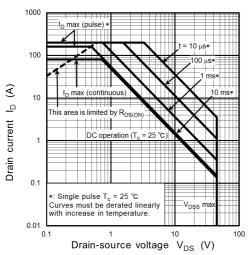


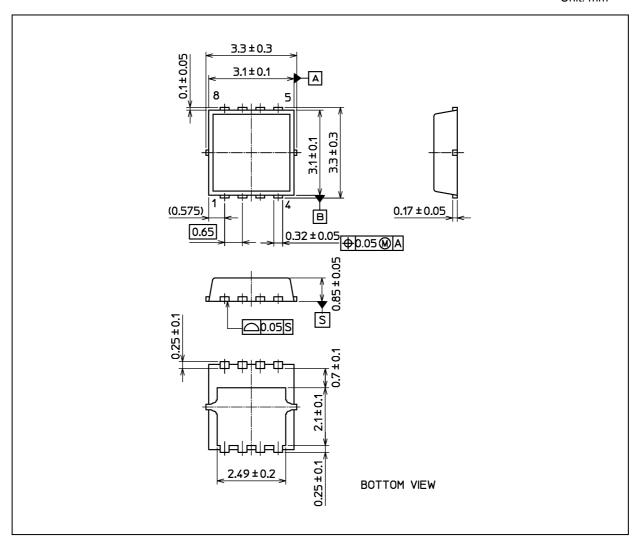
Fig. 8.16 Safe Operating Area (Guaranteed Maximum)

Note: The above characteristics curves are presented for reference only and not guaranteed by production test, unless otherwise noted.



# **Package Dimensions**

Unit: mm



Weight: 0.029 g (typ.)

| Package Name(s)        |
|------------------------|
| TOSHIBA: 2-3X1S        |
| Nickname: TSON Advance |



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